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		APPLICANT Luc OUELLET et al.					
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U.S. PATENT DOCUMENTS							
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FOREIGN PATENT DOCUMENTS							
		Document Number	Date	Country	Class	Sub Class	Translation Yes No
OTHER DOCUMENTS (Including Author, title, Date, Pertinent Pages, Etc.)							
wn		D.K.W. Lam, "Low temperature plasma chemical vapor deposition of silicon oxynitride thin-film waveguides", Applied Optics, Vol. 23, No. 16, August 15, 1984, pp. 2744-2746.					
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EXAMINER <i>Wes Man</i>		DATE CONSIDERED 10/6/03					

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EXAMINER Ws M...		DATE CONSIDERED 10/8/03					
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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))			Docket No. 10932-US
In Re Application Of: Luc OUELLET, et al.			
Serial No. 09/833,711	Filing Date 13 April 2001	Examiner	Group Art Unit 2874
Title: OPTICAL QUALITY SILICA FILMS			
<p style="text-align: center;">Address to: Assistant Commissioner for Patents Washington, D.C. 20231</p> <p style="text-align: center;">37 CFR 1.97 (b)</p> <p>1. <input checked="" type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed within three months of the filing of a national application; within three months of the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or before the mailing date of a first Office Action on the merits, whichever event occurs last.</p> <p style="text-align: center;">37 CFR 1.97 (c)</p> <p>2. <input type="checkbox"/> The Information Disclosure Statement submitted herewith is being filed after three months of the filing of a national application, or the date of entry of the national stage as set forth in 37 CFR 1.491 in an international application; or after the mailing date of a first Office Action on the merits, whichever occurred last but before the mailing date of either:</p> <p style="padding-left: 40px;">1. a Final Action under 37 CFR 1.113, or</p> <p style="padding-left: 40px;">2. a Notice of Allowance under 37 CFR 1.311,</p> <p style="padding-left: 40px;">whichever occurs first.</p> <p>Also submitted herewith is:</p> <p><input type="checkbox"/> a certification as specified in 37 CFR 1.97(e);</p> <p style="text-align: center;">OR</p> <p><input type="checkbox"/> the fee set forth in 37 CFR 1.17(p) for submission of an Information Disclosure Statement under 37 CFR 1.97(c).</p>			

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TRANSMITTAL OF INFORMATION DISCLOSURE STATEMENT (Under 37 CFR 1.97(b) or 1.97(c))	Docket No. 10932-US
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In Re Application Of: Luc OUELLET, et al.

Serial No. 09/833,711	Filing Date 13 April 2001	Examiner	Group Art Unit 2874
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Title: OPTICAL QUALITY SILICA FILMS

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